



**INFORMATION DISCLOSURE STATEMENT**

Applicant : Paraschiv, et al.  
App. No. : 10/797888  
Filed : March 9, 2004  
For : METHOD FOR SELECTIVE REMOVAL  
OF HIGH-K MATERIAL  
Examiner : Unassigned  
Group Art Unit : Unknown

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing 4 references that are also enclosed.

This Information Disclosure Statement is being filed before the receipt of a first Office Action on the merits, and presumably no fee is required in accordance with 37 C.F.R. § 1.97(b)(3). If a first Office Action on the merits was mailed before the mailing date of this Statement, the Commissioner is authorized to charge the fee set forth in 37 C.F.R. § 1.17(p) to Deposit Account No. 11-1410.

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: August 24, 2004

By: 

Rose M. Thiessen  
Registration No. 40,202  
Attorney of Record  
Customer No. 20,995  
(619) 235-8550

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
IMEC312.001AUSAPPLICATION NO.  
10/797888INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT

(SEE SEVERAL SHEETS IF NECESSARY)

APPLICANT  
Paraschiv, et al.FILING DATE  
09-Mar-2004GROUP  
1763

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1	2003-0104706-A1		Mitsubishi et al.			

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO

EXAMINER  
INITIAL

## OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

	2	Barnett, et al.; Solid State Phenomena, Vol. 92, p. 11, 2003; "Wet Etch Enhancement of HfO <sub>2</sub> Films by Implant Processing"
	3	Saenger, et al.; MRS Symposium Proceedings, Volume 745 (Novel Materials and Processes for advanced CMOS, Pennsylvania, p. 79 - 84, 2003; "A Selective Etching Process for Chemically Inert High-k Metal Oxides"
	4	Christenson, et al. Solid State Phenomena, Vol. 92, p. 129, 2003; "Selective Wet Etching of High-k Gate Dielectrics"

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060704

EXAMINER	DATE CONSIDERED
<p>*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.</p>	